

### **Inventor Information**

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### **Application Information**

Title Line One:: A METHOD FOR FORMING CRYSTALLINE  
Title Line Two:: SEMICONDUCTOR LAYERS, A METHOD FOR  
Title Line Three:: FABRICATING THIN FILM TRANSISTORS,  
Title Line Four:: AND A METHOD FOR FABRICATING SOLAR  
Title Line Five:: CELLS AND ACTIVE MATRIX LIQUID  
Title Line Six:: CRYSTAL DEVICES  
Total Drawing Sheets:: 10  
Docket Number:: 038839.02

### **Continuity Information**

>This application is a:: Division of  
Application One:: 09/400,303  
Filing Date:: September 21, 1999  
Patent Number::  
which is a:: Division of  
>>Application Two:: 08/776,545  
Filing Date:: January 31, 1997  
Patent Number:: 6,066,516

### **Prior Foreign Applications**

Foreign Application One:: 7-159147  
Filing Date:: June 26, 1995  
Country:: Japan  
Priority Claimed:: Yes  
Foreign Application Two:: 8-161280  
Filing Date:: June 21, 1996  
Country:: Japan  
Priority Claimed:: Yes

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